

Semiconductors II: surfaces, interfaces, microstructures, and related topics

GaAs(001)-“ 2×3 ” surface studied by scanning tunneling microscopy	1013
Ilya Chizhov, Geunseop Lee, Roy F. Willis, Dmitry Lubyshev, and David L. Miller	
Structural model for the Si(111)- 4×1 -In reconstruction	1017
A. A. Saranin, A.V. Zotov, K. V. Ignatovich, V. G. Lifshits, T. Numata, O. Kubo, H. Tani, M. Katayama, and K. Oura	
Random-walk mechanism for step retraction on hydrogen-etched Si(111)	1021
Mats I. Larsson, Heidrun Bethge, Ulrich Köhler, Stefan Menke, and Martin Henzler	
Differences between statistical mechanics and thermodynamics on the mesoscopic scale	1025
Alex Kamenev and Yuval Gefen	
Resistance oscillation in wide single quantum wells subject to in-plane magnetic fields	1029
T. Jungwirth, T. S. Lay, L. Smrčka, and M. Shayegan	
Optimization of intersubband resonant second-order susceptibility in asymmetric graded $\text{Al}_x\text{Ga}_{1-x}\text{As}$ quantum wells using supersymmetric quantum mechanics	1033
S. Tomić, V. Milanović, and Z. Ikonić	
Multiple cyclotron resonances in GaAs- $\text{Al}_x\text{Ga}_{1-x}\text{As}$ quantum wells detected by resonant inelastic light scattering	1037
C. Schüller, R. Krahne, G. Biese, C. Steinebach, E. Ulrichs, D. Heitmann, and K. Eberl	
Acoustic-phonon Raman scattering from Wannier-Stark levels in GaAs/AlAs superlattices	1041
V. F. Sapega, T. Ruf, M. Cardona, H. T. Grahn, and K. Ploog	
Electronic transport through one-dimensional magnetic superlattices	1045
Zhen-Li Ji and D. W. L. Sprung	
Image of local density of states fluctuations in disordered metals in the differential conductance of tunneling via a resonant impurity level	1049
Vladimir I. Fal'ko	
Many-body blockade of resonant tunneling of two-dimensional electrons	1053
J. G. S. Lok, A. K. Geim, J. C. Maan, L. Eaves, A. Nogaret, P. C. Main, and M. Henini	
Splitting of resistance peaks and anomalous Hall plateaus in asymmetric double-quantum-well structures	1057
Y. Takagaki, K. Muraki, and S. Tarucha	
Disordered critical wave functions in random-bond models in two dimensions: Random-lattice fermions at $E=0$ without doubling	1061
Yasuhiro Hatsugai, Xiao-Gang Wen, and Mahito Kohmoto	
Shape effects on conductance quantization in three-dimensional nanowires: Hard versus soft potentials	1065
E. N. Bogachek, A. G. Scherbakov, and Uzi Landman	
Conductance of atomic-scale gold contacts under high-bias voltages	1069
Hiroshi Yasuda and Akira Sakai	
Backscattering of ballistic electrons in a corrugated-gate quantum wire	1073
Y. Ochiai, A. W. Widjaja, N. Sasaki, K. Yamamoto, R. Akis, D. K. Ferry, J. P. Bird, K. Ishibashi, Y. Aoyagi, and T. Sugano	
Femtosecond four-wave-mixing studies of nearly homogeneously broadened excitons in GaN	1077
A. J. Fischer, W. Shan, G. H. Park, J. J. Song, D. S. Kim, D. S. Yee, R. Horning, and B. Goldenberg	
Dynamical Stokes shift due to interface nanoroughness in growth islands of GaAs single quantum wells	1081
Kenzo Fujiwara, Holger T. Grahn, and Klaus H. Ploog	
$(\text{NH}_4)_2\text{S}_x$ -treated InAs(001) surface studied by x-ray photoelectron spectroscopy and low-energy electron diffraction	1084
Y. Fukuda, Y. Suzuki, N. Sanada, M. Shimomura, and S. Masuda	